



DMT6005LPS

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> T <sub>C</sub> = +25°C (Note 9)
60V	4.9mΩ @ V <sub>GS</sub> = 10V	100A

# **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- High Frequency Switching
- Sync. Rectification
- DCDC Converters

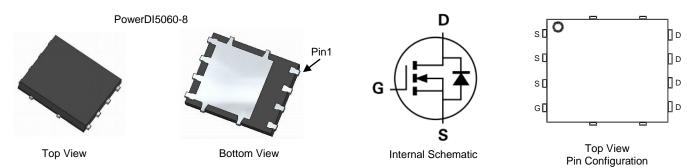
### 60V N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

### Features

- 100% Unclamped Inductive Switching ensures more reliable and robust end application
- Low R<sub>DS(ON)</sub> minimizes power losses
- Low Q<sub>g</sub> minimizes switching losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: PowerDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 <sup>(3)</sup>
- Weight: 0.097 grams (Approximate)



## Ordering Information (Note 4)

h		
Part Number	Case	Packaging
DMT6005LPS-13	PowerDI5060-8	2,500 / Tape & Reel

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

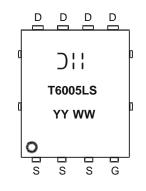
 See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**

Notes:



)'! = Manufacturer's Marking T6005LS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 16 = 2016) WW = Week (01 to 53)



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V <sub>DSS</sub>	60	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 5)	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	17.9 14.3	A
Continuous Drain Current (Note 6)	T <sub>C</sub> = +25°C (Note 9)	ID	100	A
	T <sub>C</sub> = +100°C		90	
Maximum Continuous Body Diode Forward Current (Note 6)	ls	100	A	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)		I <sub>DM</sub>	160	A
Avalanche Current, L=1mH		I <sub>AS</sub>	14.8	A
Avalanche Energy, L=1mH		E <sub>AS</sub>	98	mJ

### **Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)		R <sub>θJA</sub>	47	°C/W
Total Power Dissipation (Note 6)	T <sub>C</sub> = +25°C	PD	125	W
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	1	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

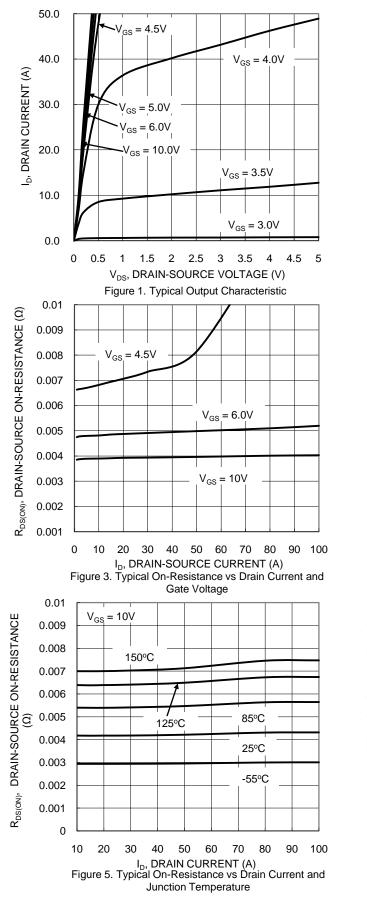
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						-	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	-	-	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	-	3	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	P	-	3.9	4.9	mΩ	$V_{GS} = 10V, I_D = 50A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	7.6	8.5		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 12.5A	
Diode Forward Voltage	V <sub>SD</sub>	-	0.9	-	V	$V_{GS} = 0V, I_{S} = 50A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	-	2962	-		$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	C <sub>oss</sub>	-	965.2	-	pF		
Reverse Transfer Capacitance	Crss	-	59.8	-			
Gate Resistance	Rg	-	0.66	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	-	47.1	-			
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	-	23.1	-	nC	$V_{DD} = 30V, I_D = 50A$	
Gate-Source Charge	Q <sub>gs</sub>	-	10.2	-	no		
Gate-Drain Charge	Q <sub>gd</sub>	-	12.5	-			
Turn-On Delay Time	t <sub>D(ON)</sub>	-	8.3	-			
Turn-On Rise Time	t <sub>R</sub>	-	9.4	-		$V_{DD} = 30V, V_{GS} = 10V,$ $I_D = 30A, R_G = 3.3\Omega$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	22	-	ns		
Turn-Off Fall Time	t <sub>F</sub>	-	8.9	-			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	-	40.4	-	ns		
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	-	49.7	-	nC	— I <sub>F</sub> = 30A, di/dt = 100A/μs	

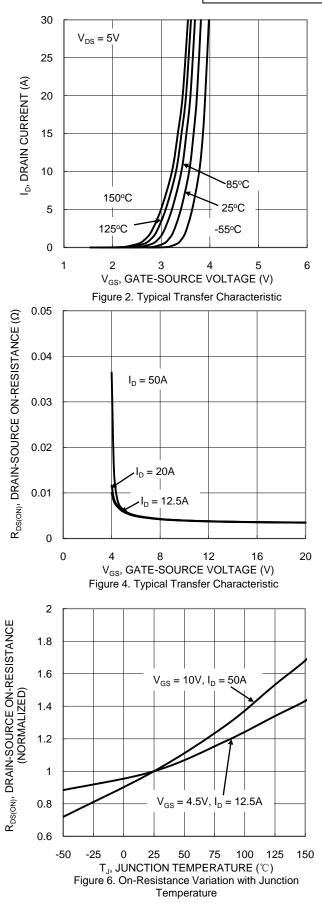
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).
Short duration pulse test used to minimize self-heating effect. Notes:

B. Guaranteed by design. Not subject to product testing.
Package limited.





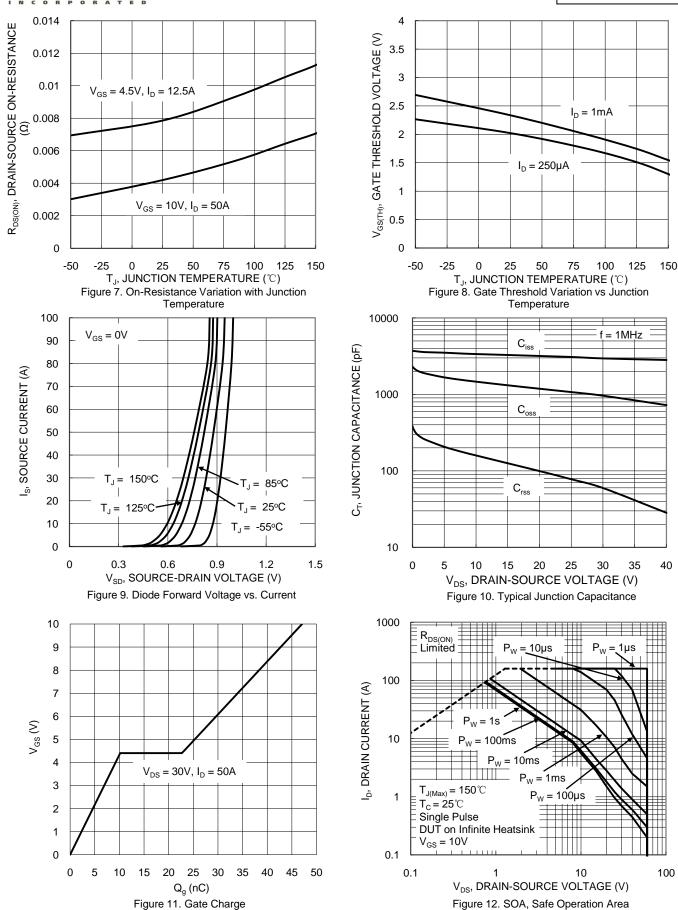




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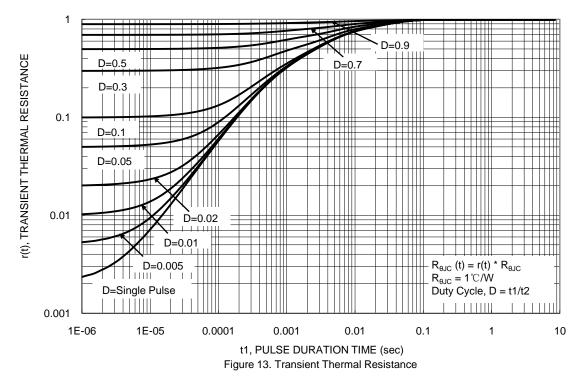






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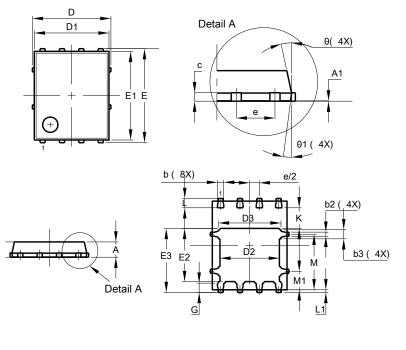




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8

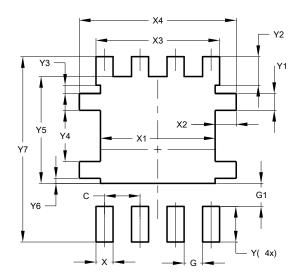


	PowerDI5060-8					
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0.00	0.05				
b	0.33	0.51	0.41			
b2	0.200	0.350	0.273			
b3	0.40	0.80	0.60			
С	0.230	0.330	0.277			
D	-	5.15 BSC				
D1	4.70	5.10	4.90			
D2	3.70	4.10	3.90			
D3	3.90	4.30	4.10			
E	(	6.15 BSC				
E1	5.60	6.00	5.80			
E2	3.28	3.68	3.48			
E3	3.99	4.39	4.19			
е	1.27 BSC					
G	0.51	0.71	0.61			
K	0.51					
L	0.51	0.71	0.61			
L1	0.100	0.200	0.175			
М	3.235	4.035	3.635			
M1	1.00	1.40	1.21			
Θ	10º	12º	11º			
Θ1	6°	8º	7°			
Al	All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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